

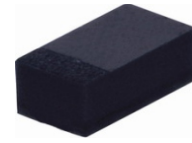
# SMD Schottky Barrier Diode



SMD Diodes Specialist

## CDBUR0140R(RoHs Device)

$I_o = 100 \text{ mA}$   
 $V_R = 40 \text{ Volts}$

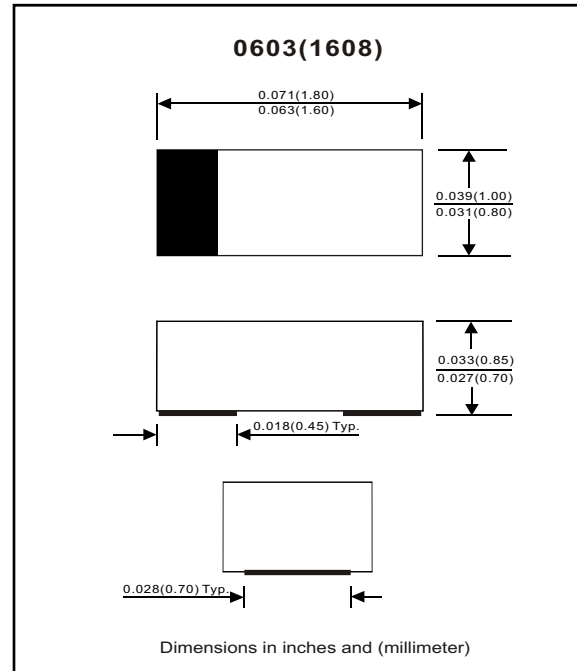


### Features

- Low reverse current.
- Designed for mounting on small surface.
- Extremely thin / leadless package.
- Majority carrier conduction.

### Mechanical data

- Case: 0603(1608) standard package, molded plastic.
- Terminals: Gold plated, solderable per MIL-STD-750, method 2026.
- Polarity: Indicated by cathode band.
- Mounting position: Any
- Weight: 0.003 gram(approx.).



### Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive Peak reverse voltage		$V_{RRM}$			45	V
Reverse voltage		$V_R$			40	V
Average forward rectified current		$I_o$			100	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	$I_{FSM}$			1	A
Storage temperature		$T_{STG}$	-40		+125	°C
Junction temperature		$T_j$			+125	°C

### Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 10 \text{ mA}$	$V_F$			0.45	V
Reverse current	$V_R = 10 \text{ V}$	$I_R$			1	uA
Capacitance between terminals	$f = 1 \text{ MHz}$ , and 10 VDC reverse voltage	$C_T$		6		pF

## RATING AND CHARACTERISTIC CURVES (CDBUR0140R)

Fig. 1 - Forward characteristics

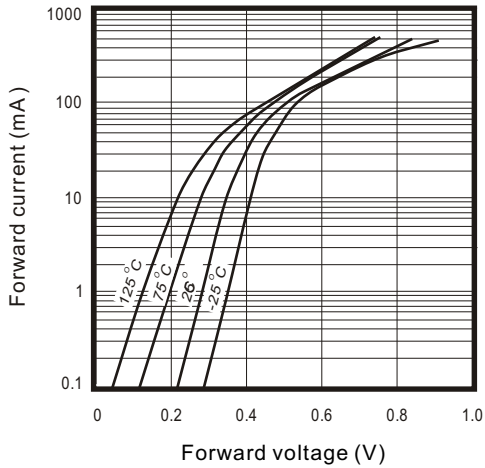


Fig. 2 - Reverse characteristics

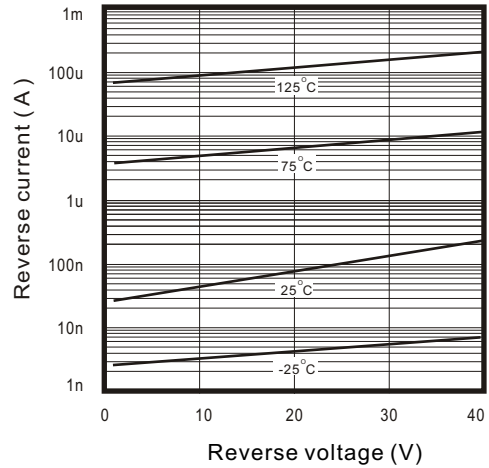


Fig. 3 - Capacitance between terminals characteristics

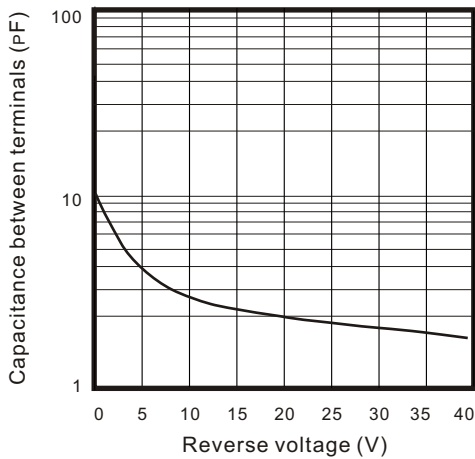


Fig. 4 - Current derating curve

